NL17SH04

Single Inverter

The NL17SH04 is an advanced high speed CMOS inverter fabricated with silicon gate CMOS technology.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output.

The NL17SH04 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the NL17SH04 to be used to interface 5 V circuits to 3 V circuits.

Features

- High Speed: t_{PD} = 3.5 ns (Typ) at V_{CC} = 5 V
- Low Power Dissipation: $I_{CC} = 1 \ \mu A (Max)$ at $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- These are Pb–Free Devices



ON Semiconductor®

http://onsemi.com







D = Specific Device Code



| PIN ASSIGNMENT | | | | | |
|----------------|-----------------|--|--|--|--|
| 1 | IN A | | | | |
| 2 | GND | | | | |
| 3 | NC | | | | |
| 4 | OUT 7 | | | | |
| 5 | V _{CC} | | | | |

FUNCTION TABLE

| A Input | Y Output |
|---------|-----------------|
| L | Н |
| Н | L |

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

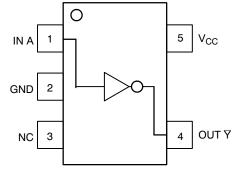


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|----------------------|---|-------------------------------|------|
| V _{CC} | DC Supply Voltage | -0.5 to +7.0 | V |
| V _{IN} | DC Input Voltage | -0.5 to +7.0 | V |
| V _{OUT} | DC Output Voltage | –0.5 to V _{CC +} 0.5 | V |
| l _{IK} | DC Input Diode Current | -20 | mA |
| I _{OK} | DC Output Diode Current | ±20 | mA |
| I _{OUT} | DC Output Current | ±25 | mA |
| I _{CC} | DC Supply Current per Supply Pin | 50 | mA |
| T _{STG} | Storage Temperature Range | -65 to +150 | °C |
| ΤL | Lead Temperature, 1 mm from Case for 10 Seconds | 260 | °C |
| ТJ | Junction Temperature Under Bias | +150 | °C |
| PD | Power Dissipation in Still Air | 50 | mW |
| MSL | Moisture Sensitivity | Level 1 | |
| F _R | Flammability Rating Oxygen Index: 28 to 34 | UL 94 V-0 @ 0.125 in | |
| I _{Latchup} | Latchup Performance Above V _{CC} and Below GND at 125°C (Note 1) | ±100 | mA |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Characteristics | Min | Max | Unit |
|---------------------------------|--|--------|-----------------|------|
| V _{CC} | DC Supply Voltage | 2.0 | 5.5 | V |
| V _{IN} | DC Input Voltage | 0.0 | 5.5 | V |
| V _{OUT} | DC Output Voltage | 0.0 | V _{CC} | V |
| T _A | Operating Temperature Range | -55 | +125 | °C |
| t _r , t _f | Input Rise and Fall Time $\begin{array}{ll} V_{CC}=3.3~V\pm0.3~V\\ V_{CC}=5.0~V\pm0.5~V \end{array}$ | 0 0 | 100 20 | ns/V |

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

| Junction Temperature °C | Time, Hours | Time, Years |
|----------------------------|-------------|-------------|
| 80 | 1,032,200 | 117.8 |
| 90 | 419,300 | 47.9 |
| 100 | 178,700 | 20.4 |
| 110 | 79,600 | 9.4 |
| 120 | 37,000 | 4.2 |
| 130 | 17,800 | 2.0 |
| 140 | 8,900 | 1.0 |

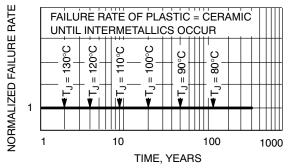


Figure 3. Failure Rate vs. Time Junction Temperature

| | | | V _{CC} | 1 | A = 25°C | 2 | T _A ≤ | 85°C | -55°C 1 | o 125°C | |
|-----------------|--|--|--------------------------|----------------------------|-------------------|----------------------------|----------------------------|----------------------------|----------------------------|----------------------------|------|
| Symbol | Parameter | Test Conditions | (V) | Min | Тур | Max | Min | Max | Min | Мах | Unit |
| VIH | Minimum High-Level Input Voltage | | 2.0 3.0 4.5 5.5 | 1.5 2.1 3.15 3.85 | | | 1.5 2.1 3.15 3.85 | | 1.5 2.1 3.15 3.85 | | V |
| V _{IL} | Maximum Low-Level Input Voltage | | 2.0 3.0 4.5 5.5 | | | 0.5 0.9 1.35 1.65 | | 0.5 0.9 1.35 1.65 | | 0.5 0.9 1.35 1.65 | V |
| V _{OH} | Minimum High–Level Output Voltage V _{IN} = V _{IH} or V _{IL} | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu \text{A}$ | 2.0 3.0 4.5 | 1.9 2.9 4.4 | 2.0 3.0 4.5 | | 1.9 2.9 4.4 | | 1.9 2.9 4.4 | | V |
| | | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $l_{OH} = -4 \text{ mA}$ $l_{OH} = -8 \text{ mA}$ | 3.0 4.5 | 2.58 3.94 | | | 2.48 3.80 | | 2.34 3.66 | | |
| V _{OL} | Maximum Low–Level Output Voltage V _{IN} = V _{IH} or V _{IL} | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu A$ | 2.0 3.0 4.5 | | 0.0 0.0 0.0 | 0.1 0.1 0.1 | | 0.1 0.1 0.1 | | 0.1 0.1 0.1 | V |
| | | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$ | 3.0 4.5 | | | 0.36 0.36 | | 0.44 0.44 | | 0.52 0.52 | |
| I _{IN} | Maximum Input Leakage Current | $V_{IN} = 5.5 \text{ V or GND}$ | 0 to 5.5 | | | ±0.1 | | ±1.0 | | ±1.0 | μΑ |
| Icc | Maximum Quiescent Supply Current | $V_{IN} = V_{CC}$ or GND | 5.5 | | | 1.0 | | 10 | | 40 | μΑ |

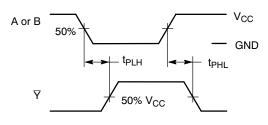
DC ELECTRICAL CHARACTERISTICS

AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0$ ns

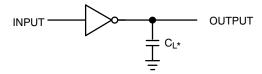
| | | | T _A = 25°C | | T _A ≤ 85°C | | $\textbf{-55} \leq \textbf{T}_{\textbf{A}} \leq \textbf{125}^{\circ}\textbf{C}$ | | | |
|---|---|---|-----------------------|-------------|-----------------------|-------------|---|------------------------|-------------|------|
| Symbol | Parameter | Test Conditions | Min | Тур | Max | Min | Max | Min | Max | Unit |
| t _{PLH} , Maximum t _{PHL} Propagation Delay, | $\begin{array}{c} V_{CC} = 3.3 \pm 0.3 \; V \ \ C_L = 15 \; pF \\ C_L = 50 \; pF \end{array}$ | | 4.5 6.4 | 7.1 10.6 | | 8.5 12.0 | | 10.0 14.5 | ns | |
| | Input A to Y | $V_{CC} = 5.0 \pm 0.5 \text{ V} \begin{array}{c} C_L = 15 \text{ pF} \\ C_L = 50 \text{ pF} \end{array}$ | | 3.5 4.5 | 5.5 7.5 | | 6.5 8.5 | | 8.0 10.0 | |
| C _{IN} | Maximum Input Capacitance | | | 4 | 10 | | 10 | | 10 | pF |
| | | | | | | Турі | cal @ 25 | 5°C, V _{CC} = | 5.0 V | |
| C | Power Dissination Ca | nacitanco (Noto 2) | | | | | | 8.0 | | nE |

 C_{PD} Power Dissipation Capacitance (Note 2)8.0pF2. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NL17SH04







*Includes all probe and jig capacitance. A 1–MHz square input wave is recommended for propagation delay tests.

Figure 5. Test Circuit

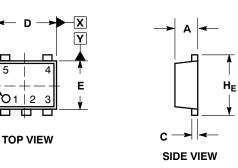
ORDERING INFORMATION

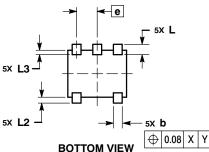
| Device | Package | Shipping [†] |
|---------------|----------------------|-----------------------|
| NL17SH04P5T5G | SOT–953 (Pb–Free) | 8000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E





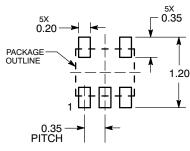
PIN ONE

NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

- CONTROLLING DIMENSION: MILLIMETERS
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- MINIMUM THICKNESS OF THE BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| TEACH, THO THOUGOIDING, OH C | | | | | | | |
|------------------------------|-------------|---------|------|--|--|--|--|
| | MILLIMETERS | | | | | | |
| DIM | MIN | MIN NOM | | | | | |
| Α | 0.34 | 0.37 | 0.40 | | | | |
| b | 0.10 | 0.15 | 0.20 | | | | |
| С | 0.07 | 0.12 | 0.17 | | | | |
| D | 0.95 | 1.00 | 1.05 | | | | |
| Е | 0.75 | 0.80 | 0.85 | | | | |
| е | | 0.35 BS | С | | | | |
| HE | 0.95 | 1.00 | 1.05 | | | | |
| Г | 0.175 REF | | | | | | |
| L2 | 0.05 | 0.10 | 0.15 | | | | |
| L3 | | | 0.15 | | | | |

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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